

1. Scope

The present specifications shall apply to an FMNS-1106S.

2. Outline

Type	Silicon Diode
Structure	Resin Molded Flammability : UL94V-0 (Equivalent)
Applications	High Frequency Rectification

3. Absolute maximum ratings

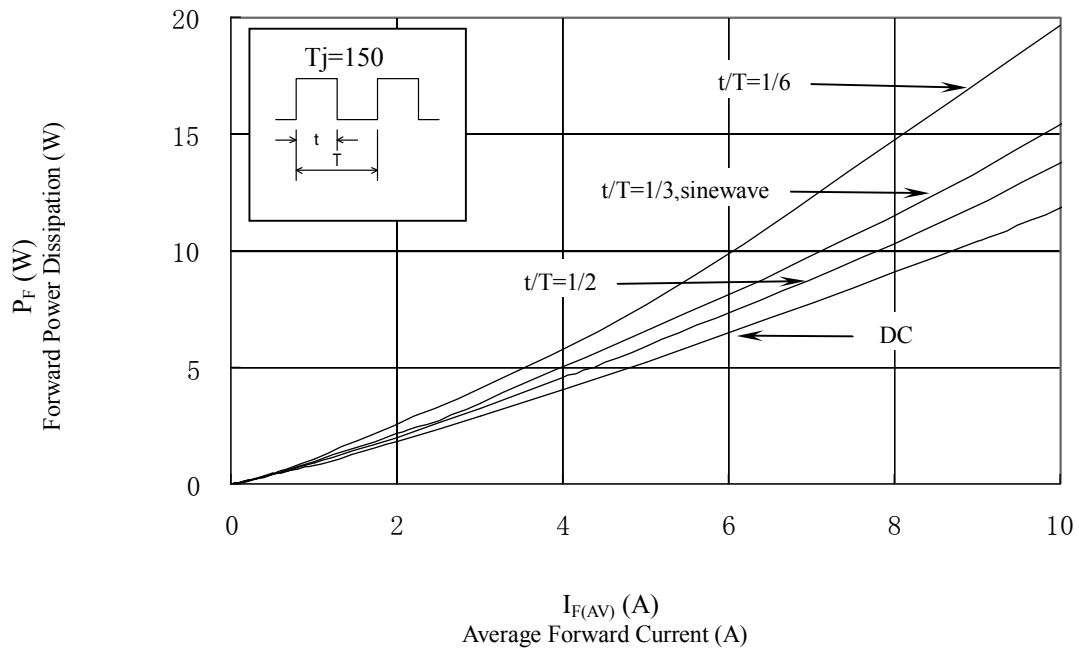
No.	Item	Symbol	Unit	Rating	Conditions
1	Transient Peak Reverse Voltage	V_{RSM}	V	600	
2	Peak Reverse Voltage	V_{RM}	V	600	
3	Average Forward Current	$I_{F(AV)}$	A	10	Refer to Derating of 6
4	Peak Surge Forward Current	I_{FSM}	A	100	10msec. Half sinewave, one shot
5	I^2t Limiting Value	I^2t	A^2s	50	$1ms \leq t \leq 10ms$
6	Junction Temperature	T_j	$^{\circ}C$	-40 ~ +150	
7	Storage Temperature	T_{stg}	$^{\circ}C$	-40 ~ +150	

4. Electrical characteristics ($T_a=25^{\circ}C$, unless otherwise specified)

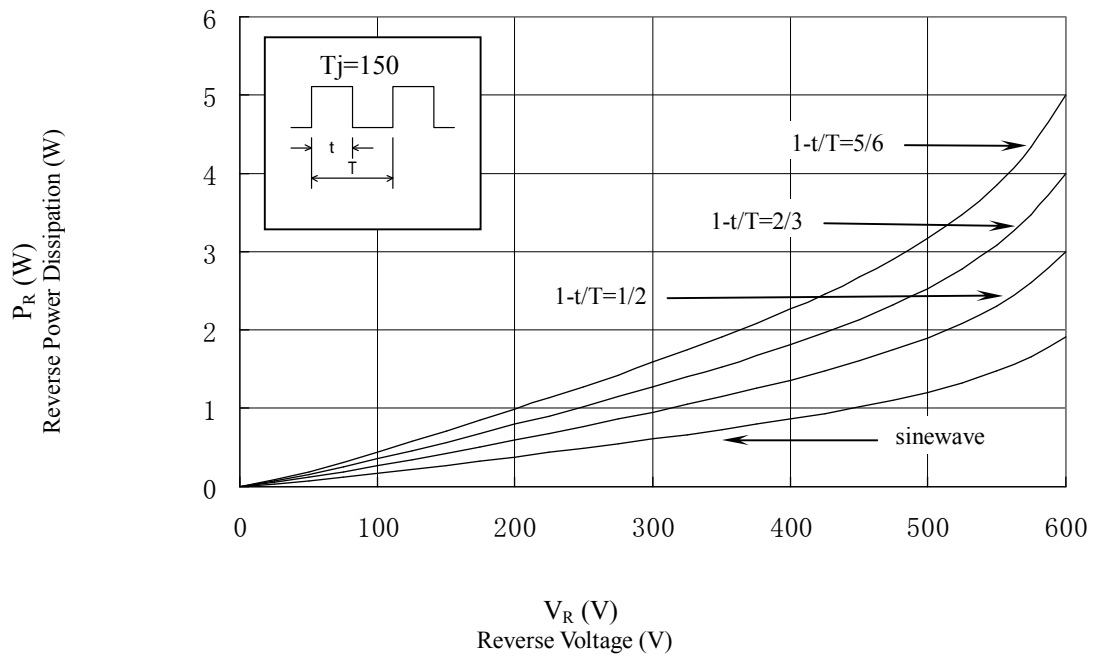
No	Item	Symbol	Unit	Value	Conditions
1	Forward Voltage Drop	V_F	V	1.3 max.	$I_F=10A$
2	Reverse Leakage Current	I_R	μA	100 max.	$V_R=V_{RM}$
3	Reverse Leakage Current Under High Temperature	$H \cdot I_R$	mA	10 max.	$V_R=V_{RM}, T_j=150^{\circ}C$
4	Reverse Recovery Time	trr1	ns	100 max.	$I_F=I_R=100mA$ 90% Recovery point, $T_j=25^{\circ}C$
		trr2	ns	50 max.	$I_F=100mA, I_R=200mA$, 75% Recovery point, $T_j=25^{\circ}C$
5	Thermal Resistance	$R_{th(j-c)}$	$^{\circ}C/W$	4.0 max.	Between Junction and case

5. Characteristics

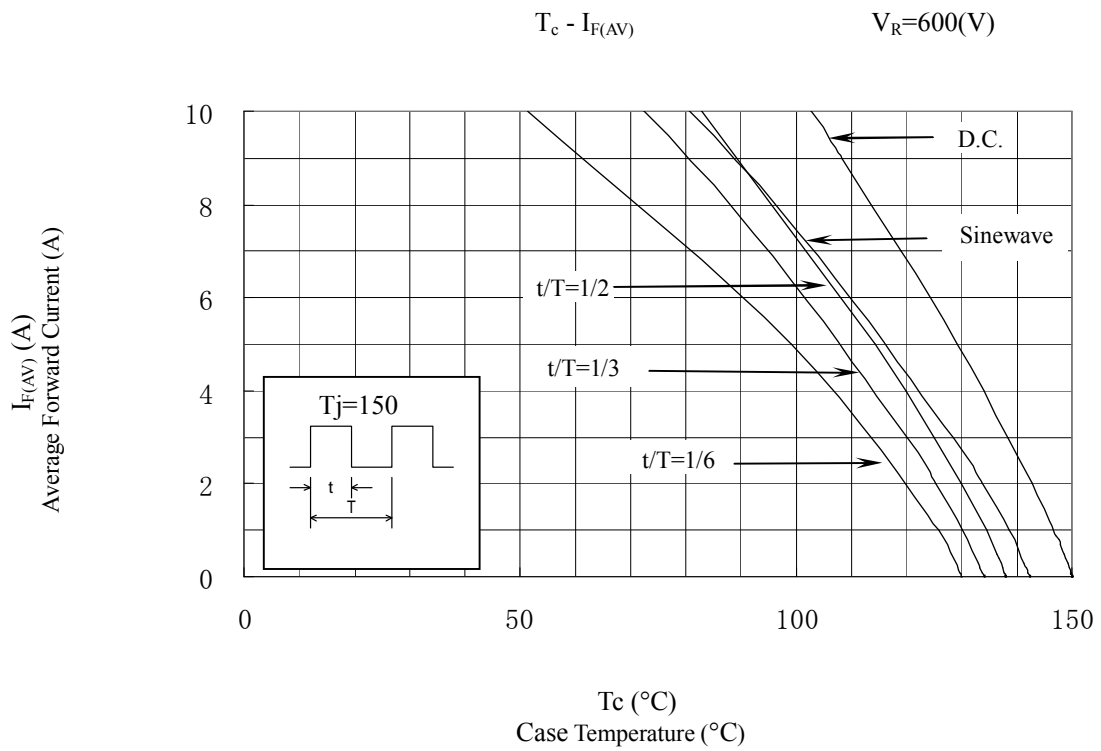
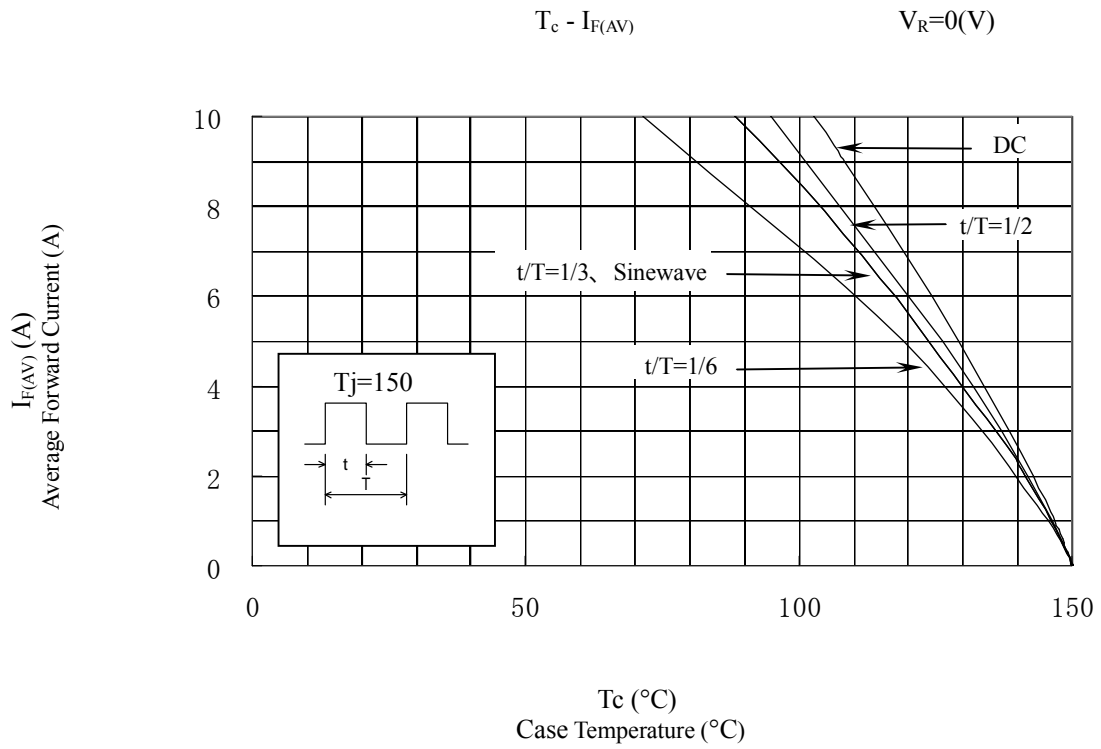
$I_{F(AV)} - P_F$



$V_R - P_R$

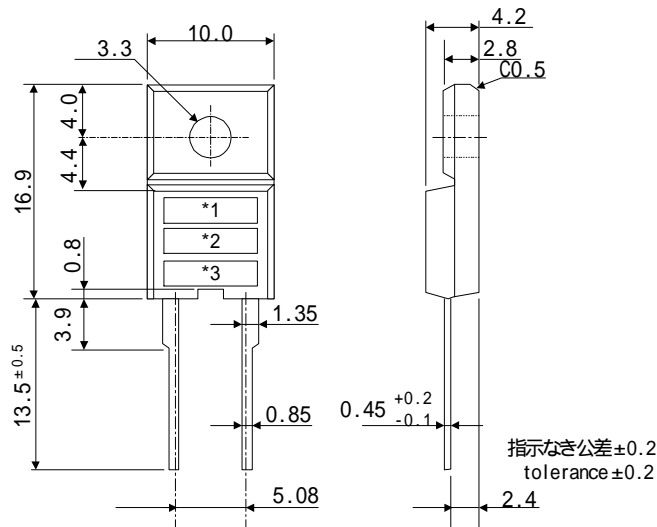


6. Derating



7. Package information

7-1 Package type, physical dimensions and material



Dimensions in mm

7-2 Appearance

The body shall be clean and shall not bear any stain, rust or flaw.

7-3 Marking

Type Name	Marking		
	* 1 Type Name	* 2 Polarity	* 3 Lot number
FMNS-1106S	NS1106	S	1st letter: Last digit of year 2nd letter: Month From 1 to 9 for Jan. to Sep., O for Oct., N for Nov., D for Dec. 3rd & 4th letter: Day ex. 5O17 (Oct. 17, 2005)